





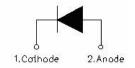
### **MBRF10200 SCHOTTKY RECTIFIER**



#### **Features**

- 150°C T<sub>J</sub> operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Circuit Diagram**



### **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{RWM} \ V_{R} \end{array}$	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	Tc=115°C	10	Α
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3ms, Half Sine pulse, T <sub>C</sub> = 25 °C	128	Α

#### **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V <sub>F1</sub>	@ 10A, Pulse, T <sub>J</sub> = 25 °C	0.85	0.95	V
	$V_{F2}$	@ 10A, Pulse, T <sub>J</sub> = 125 °C	0.73	0.85	V
Reverse Current*	I <sub>R1</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 25 °C	0.001	1.0	mA
	I <sub>R2</sub>	@V <sub>R</sub> = rated V <sub>R</sub> , T <sub>J</sub> = 125 °C	0.9	6	mA
Junction Capacitance	Ст	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C, f <sub>SIG</sub> = 1MHz	174	300	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs
RSM Isolation Voltage (t = 1.0 second, R. H. < =30%, T <sub>A</sub> = 25 °C)	V <sub>ISO</sub>	Clip mounting, the epoxy body away from the heatsink edge by more than 0.110" along the lead direction.	-	4500	V
,		Clip mounting, the epoxy body is inside the heatsink.	-	3500	
		Screw mounting, the epoxy body is inside the heatsink.	-	1500	

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%



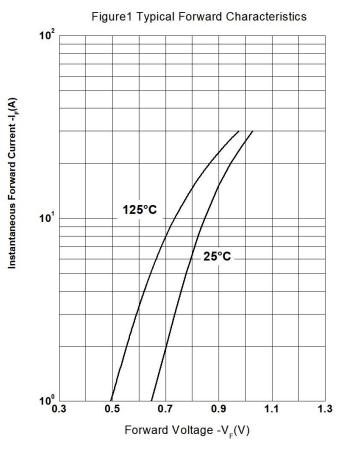


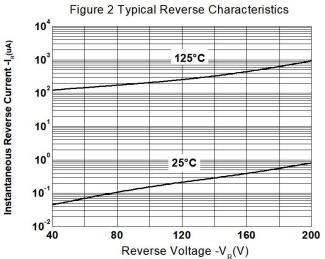


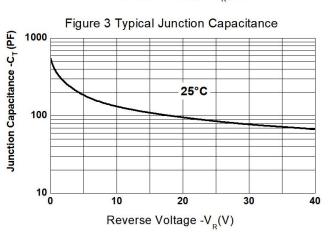
# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	4.5	°C/W
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

### **Ratings and Characteristics Curves**





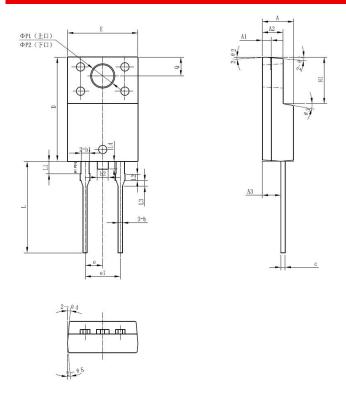






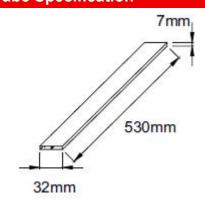


### **Mechanical Dimensions ITO-220AC**



CVMDOL	Millimeters			
SYMBOL	MIN.	TYP.	MAX.	
Α	4.30	4.50	4.70	
A1	1.10	1.30	1.50	
A2	2.80	3.00	3.20	
A3	2.50	2.70	2.90	
b	0.50	0.60	0.75	
b1	1.10	1.20	1.35	
b2	1.50	1.60	1.75	
С	0.55	0.60	0.75	
D	14.80	15.00	15.20	
E	9.96	10.16	10.36	
е	-	2.55	-	
e1	-	5.10	-	
H1	6.50	6.70	6.90	
L	12.70	13.20	13.70	
<u>L1</u>	1.60	1.80	2.00	
L2	0.80	1.00	1.20	
L3	0.60	0.80	1.00	
L4	-	1.10	1.50	
<b>ФР1</b> (上□)	3.30	3.50	3.70	
<b>ΦP2</b> (下口)	2.99	3.19	3.39	
Q	2.50	2.70	2.90	
Θ1		5°		
Θ2		4°		
Θ3		10°		
Θ4		5°		
Θ5		5°		

# **Tube Specification**



### **Marking Diagram**



Where XXXXX is YYWWL

 MBR
 = Device Type

 F
 = Package type

 10
 = Forward Current (10A)

 200
 = Reverse Voltage (200V)

 SSG
 = SSG

 YY
 = Year

 WW
 = Week

 L
 = Lot Number

**Cautions:** Molding resin Epoxy resin UL:94V-0

### **Ordering Information**

Device	Package	Shipping
MBRF10200	ITO-220AC (Pb-Free)	50 pcs/ tube







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